



**THE DATASHEET OF
MJD148T4G**



MJD148

NPN Silicon Power Transistor

DPAK for Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

Features

- High Gain
- Low Saturation Voltage
- High Current Gain – Bandwidth Product
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|----------------|---------------|--------------------------|
| Collector-Emitter Voltage | V_{CEO} | 45 | Vdc |
| Collector-Base Voltage | V_{CB} | 45 | Vdc |
| Emitter-Base Voltage | V_{EB} | 5.0 | Vdc |
| Collector Current – Continuous | I_C | 4.0 | Adc |
| Collector Current – Peak | I_{CM} | 7.0 | Adc |
| Base Current | I_B | 50 | mAdc |
| Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C | P_D | 20 0.16 | W W/ $^\circ\text{C}$ |
| Total Power Dissipation (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 1.75 0.014 | W W/ $^\circ\text{C}$ |
| Operating and Storage Junction Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |
| ESD – Human Body Model | HBM | 3B | V |
| ESD – Machine Model | MM | C | V |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

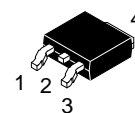
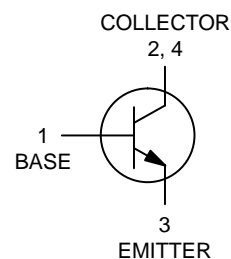
1. These ratings are applicable when surface mounted on the minimum pad sizes recommended.



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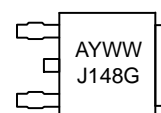
www.onsemi.com

POWER TRANSISTOR 4.0 AMPERES 45 VOLTS, 20 WATTS



DPAK
CASE 369C
STYLE 1

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
J148 = Device Code
G = Pb-Free Package

ORDERING INFORMATION

| Device | Package | Shipping† |
|--------------|-------------------|-------------------|
| MJD148T4G | DPAK (Pb-Free) | 2,500/Tape & Reel |
| NJVMJD148T4G | DPAK (Pb-Free) | 2,500/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------|------|-----------------------------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 6.25 | $^{\circ}\text{C}/\text{W}$ |
| Thermal Resistance, Junction-to-Ambient (Note 2) | $R_{\theta JA}$ | 71.4 | $^{\circ}\text{C}/\text{W}$ |

2. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$, unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|----------------|--------|-----|-----|------|
|----------------|--------|-----|-----|------|

OFF CHARACTERISTICS

| | | | | |
|---|----------------|----|----|-----------------|
| Collector-Emitter Sustaining Voltage (Note 3) ($I_C = 100 \text{ mAdc}$, $I_B = 0$) | $V_{CEO(sus)}$ | 45 | - | Vdc |
| Collector Cutoff Current ($V_{CB} = 45 \text{ Vdc}$, $I_E = 0$) | I_{CBO} | - | 20 | μAdc |
| Emitter Cutoff Current ($V_{BE} = 5 \text{ Vdc}$, $I_C = 0$) | I_{EBO} | - | 1 | mAdc |

ON CHARACTERISTICS (Note 3)

| | | | | |
|---|---------------|----------------------|--------------------|-----|
| DC Current Gain ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5 \text{ Vdc}$) ($I_C = 0.5 \text{ Adc}$, $V_{CE} = 1 \text{ Vdc}$) ($I_C = 2 \text{ Adc}$, $V_{CE} = 1 \text{ Vdc}$) ($I_C = 3 \text{ Adc}$, $V_{CE} = 1 \text{ Vdc}$) | h_{FE} | 40 85 50 30 | - 375 - - | - |
| Collector-Emitter Saturation Voltage ($I_C = 2 \text{ Adc}$, $I_B = 0.2 \text{ Adc}$) | $V_{CE(sat)}$ | - | 0.5 | Vdc |
| Base-Emitter On Voltage ($I_C = 2 \text{ Adc}$, $V_{CE} = 1 \text{ Vdc}$) | $V_{BE(on)}$ | - | 1.1 | Vdc |

DYNAMIC CHARACTERISTICS

| | | | | |
|---|-------|---|---|-----|
| Current-Gain-Bandwidth Product ($I_C = 250 \text{ mAdc}$, $V_{CE} = 1 \text{ Vdc}$, $f = 1 \text{ MHz}$) | f_T | 3 | - | MHz |
|---|-------|---|---|-----|

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS

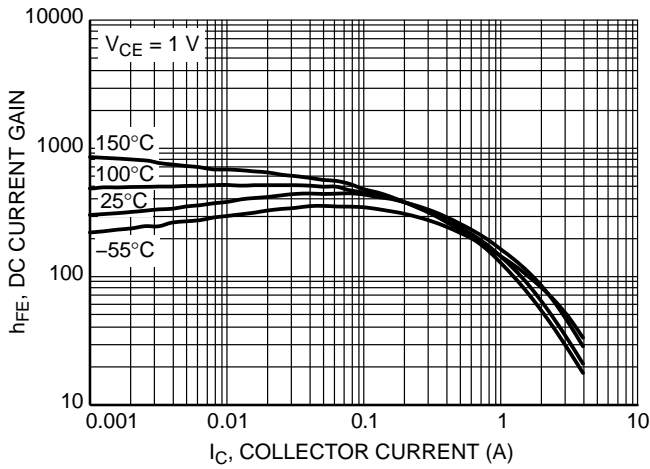


Figure 1. DC Current Gain

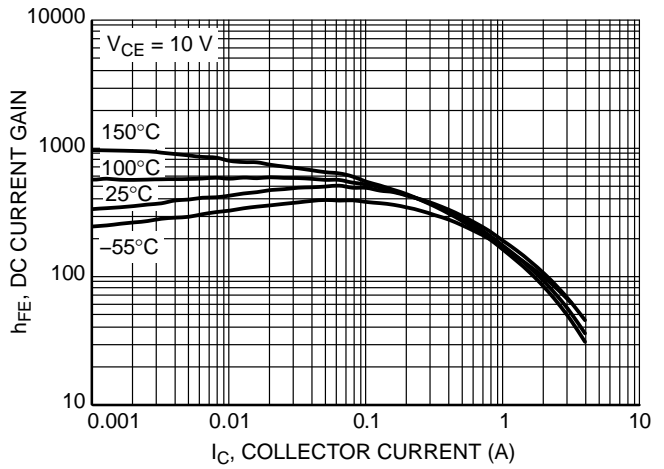


Figure 2. DC Current Gain

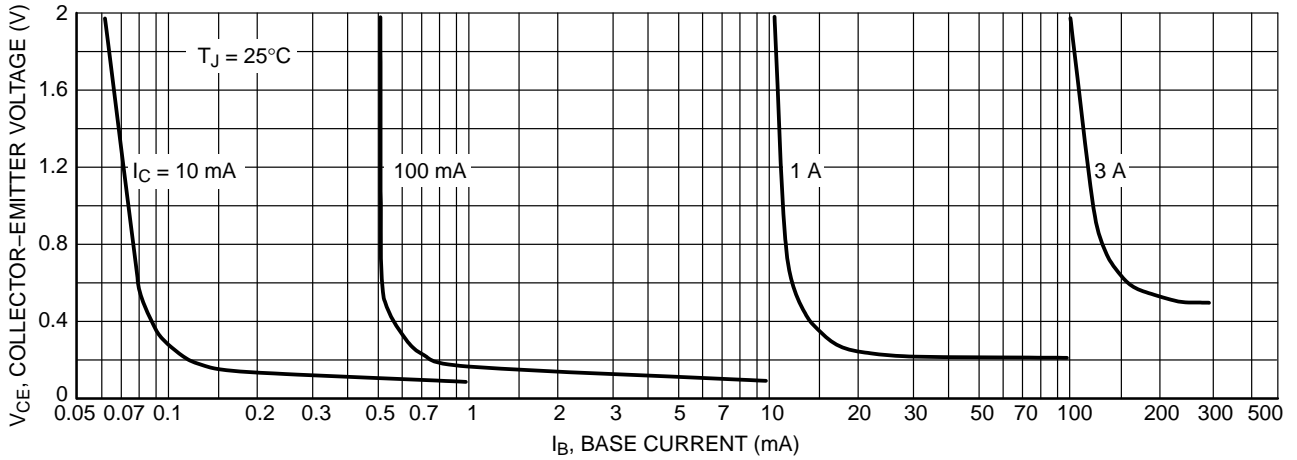


Figure 3. Collector Saturation Region

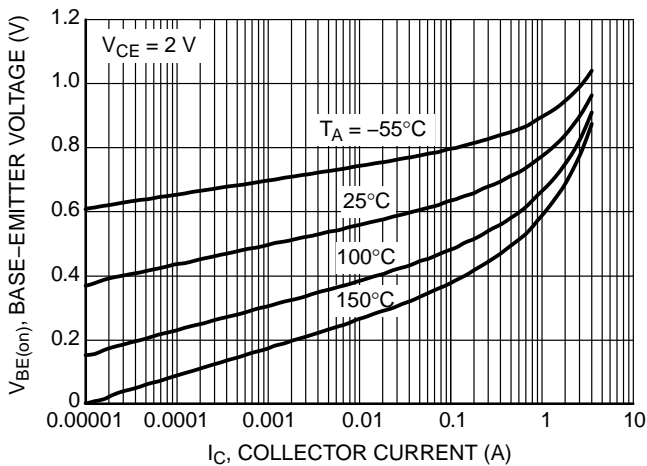


Figure 4. Base Emitter Voltage vs. Collector Current

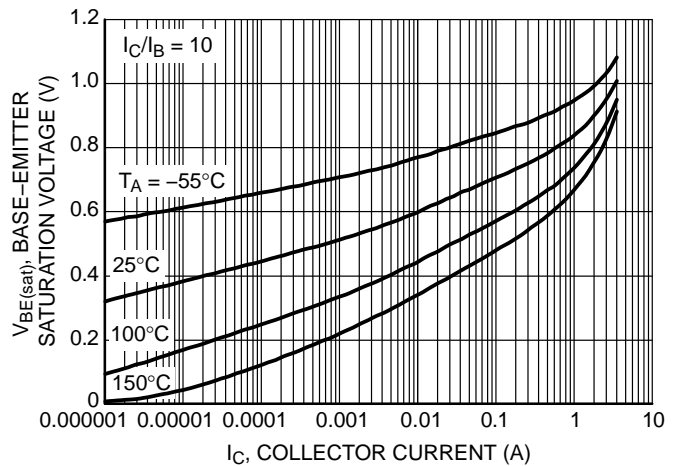


Figure 5. Base Emitter Saturation Voltage vs. Collector Current

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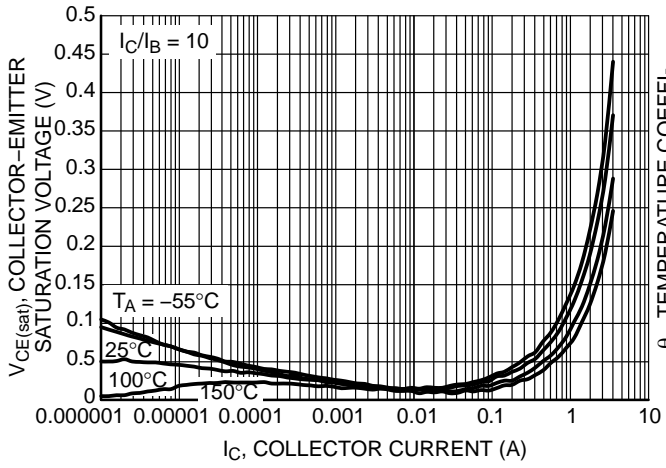


Figure 6. Collector Emitter Saturation Voltage vs. Collector Current

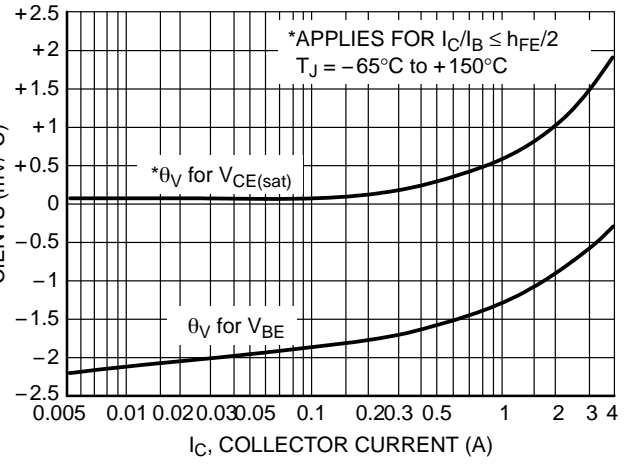


Figure 7. Temperature Coefficients

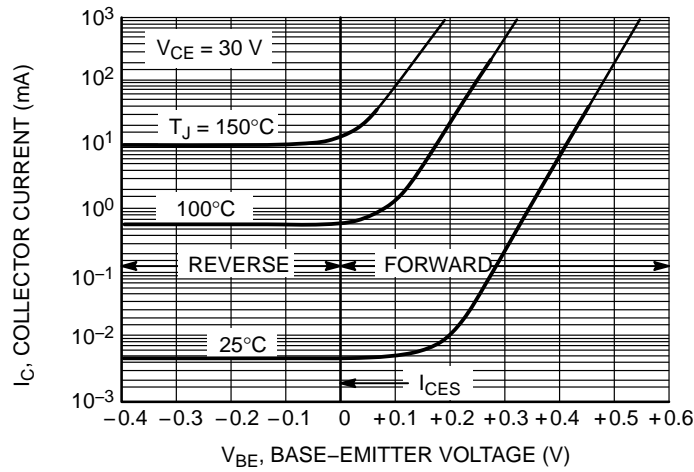


Figure 8. Collector Cut-Off Region

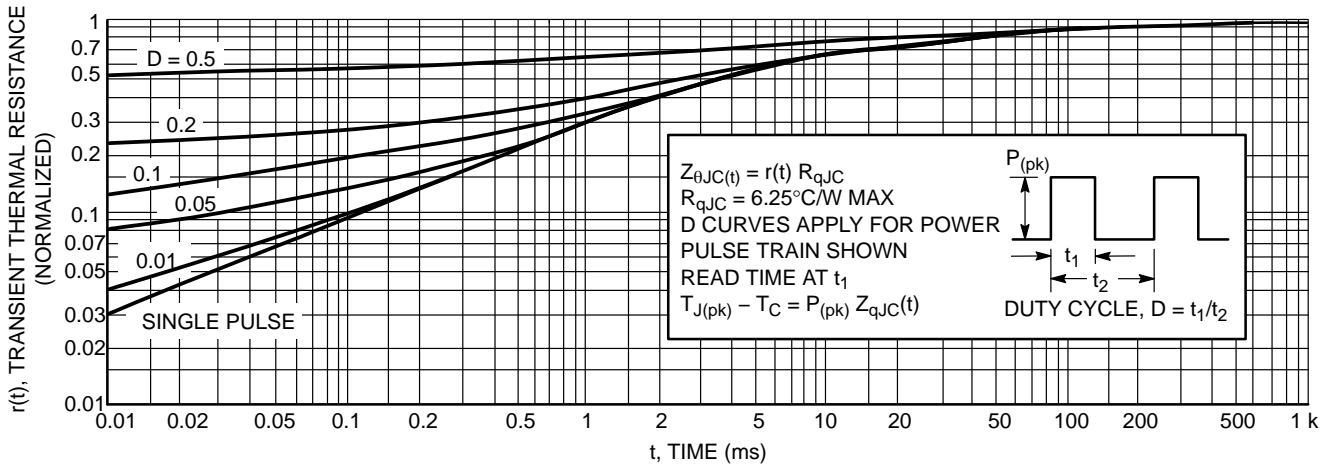


Figure 9. Thermal Response

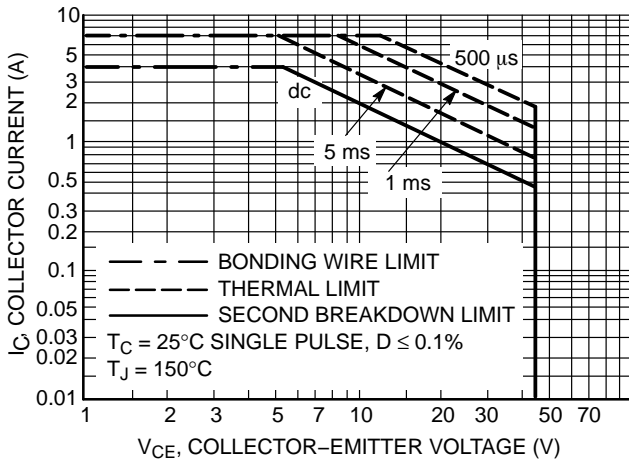


Figure 10. Maximum Rated Forward Bias

Forward Bias Safe Operating Area Information

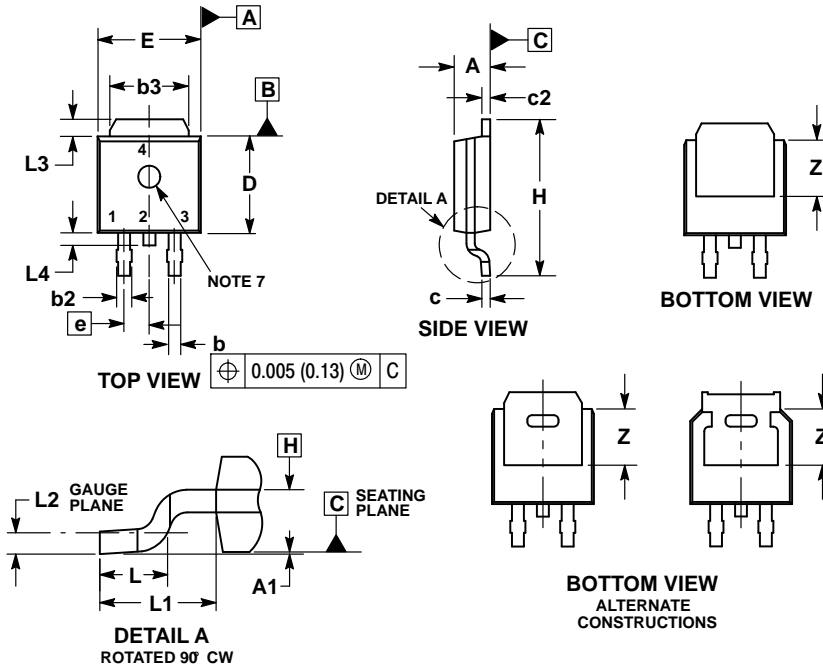
There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 10 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 9. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

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PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE) CASE 369C ISSUE F

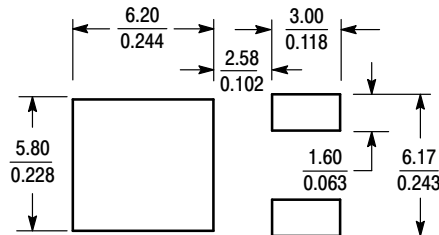


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

| DIM | INCHES | | MILLIMETERS | |
|-----|-----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.086 | 0.094 | 2.18 | 2.38 |
| A1 | 0.000 | 0.005 | 0.00 | 0.13 |
| b | 0.025 | 0.035 | 0.63 | 0.89 |
| b2 | 0.028 | 0.045 | 0.72 | 1.14 |
| b3 | 0.180 | 0.215 | 4.57 | 5.46 |
| c | 0.018 | 0.024 | 0.46 | 0.61 |
| c2 | 0.018 | 0.024 | 0.46 | 0.61 |
| D | 0.235 | 0.245 | 5.97 | 6.22 |
| E | 0.250 | 0.265 | 6.35 | 6.73 |
| e | 0.090 BSC | | 2.29 BSC | |
| H | 0.370 | 0.410 | 9.40 | 10.41 |
| L | 0.055 | 0.070 | 1.40 | 1.78 |
| L1 | 0.114 REF | | 2.90 REF | |
| L2 | 0.020 BSC | | 0.51 BSC | |
| L3 | 0.035 | 0.050 | 0.89 | 1.27 |
| L4 | --- | 0.040 | --- | 1.01 |
| Z | 0.155 | --- | 3.93 | --- |

SOLDERING FOOTPRINT*



SCALE 3:1 (mm / inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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